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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	300MHz
Co-Processors/DSP	-
RAM Controllers	-
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	-
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	360-BCBGA, FCCBGA
Supplier Device Package	360-CBGA (25x25)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc755brx300le

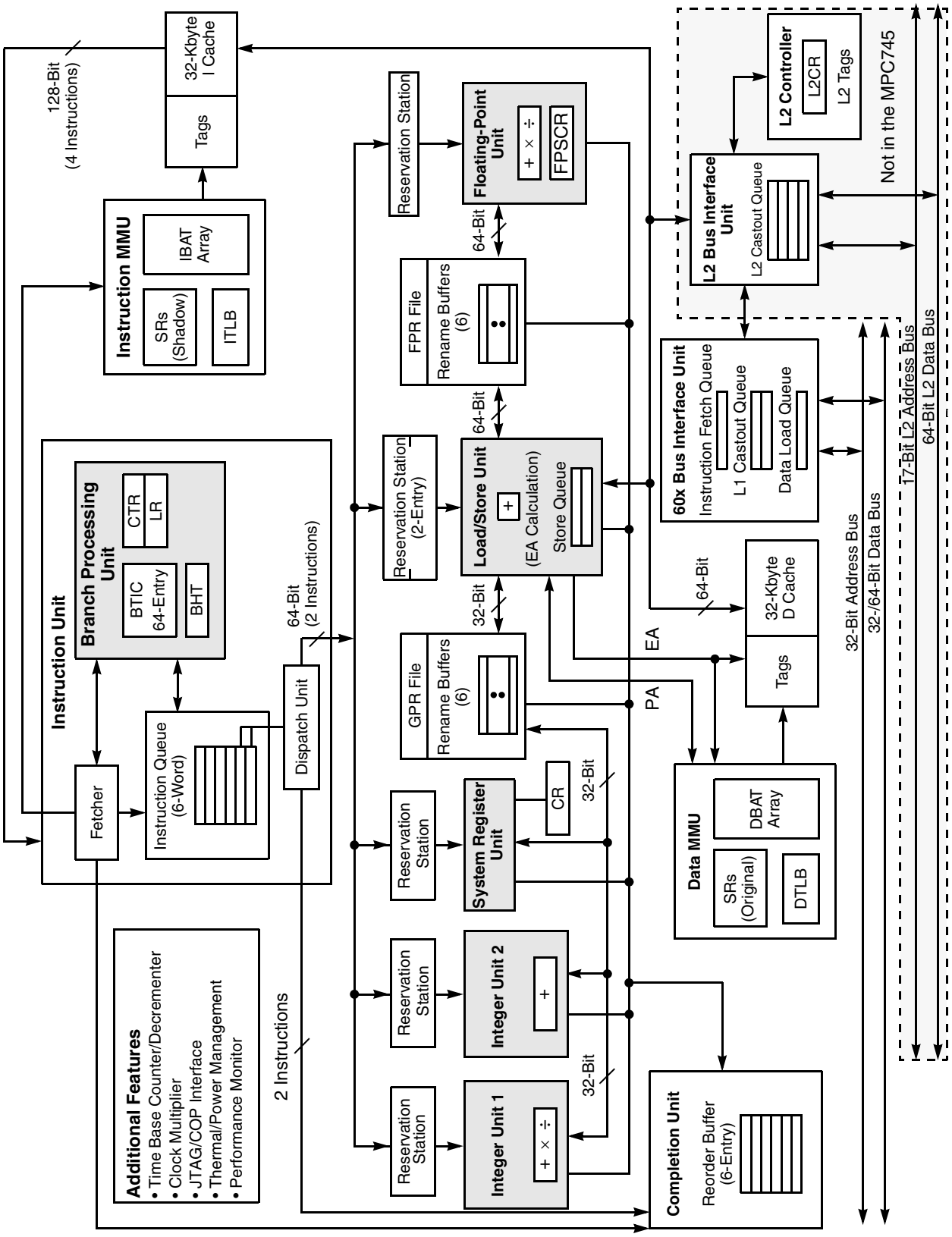


Figure 1. MPC755 Block Diagram

  - Three-cycle latency, one-cycle throughput, double-precision add
  - Four-cycle latency, two-cycle throughput, double-precision multiply-add
- System unit
  - Executes CR logical instructions and miscellaneous system instructions
  - Special register transfer instructions
- Load/store unit
  - One-cycle load or store cache access (byte, half-word, word, double word)
  - Effective address generation
  - Hits under misses (one outstanding miss)
  - Single-cycle unaligned access within double-word boundary
  - Alignment, zero padding, sign extend for integer register file
  - Floating-point internal format conversion (alignment, normalization)
  - Sequencing for load/store multiples and string operations
  - Store gathering
  - Cache and TLB instructions
  - Big- and little-endian byte addressing supported
- Level 1 cache structure
  - 32K, 32-byte line, eight-way set-associative instruction cache (iL1)
  - 32K, 32-byte line, eight-way set-associative data cache (dL1)
  - Cache locking for both instruction and data caches, selectable by group of ways
  - Single-cycle cache access
  - Pseudo least-recently-used (PLRU) replacement
  - Copy-back or write-through data cache (on a page per page basis)
  - MEI data cache coherency maintained in hardware
  - Nonblocking instruction and data cache (one outstanding miss under hits)
  - No snooping of instruction cache
- Level 2 (L2) cache interface (not implemented on MPC745)
  - Internal L2 cache controller and tags; external data SRAMs
  - 256K, 512K, and 1 Mbyte two-way set-associative L2 cache support
  - Copy-back or write-through data cache (on a page basis, or for all L2)
  - Instruction-only mode and data-only mode
  - 64-byte (256K/512K) or 128-byte (1M) sectored line size
  - Supports flow through (register-buffer) synchronous BurstRAMs, pipelined (register-register) synchronous BurstRAMs (3-1-1-1 or strobeless 4-1-1-1) and pipelined (register-register) late write synchronous BurstRAMs
  - L2 configurable to cache, private memory, or split cache/private memory
  - Core-to-L2 frequency divisors of ÷1, ÷1.5, ÷2, ÷2.5, and ÷3 supported
  - 64-bit data bus

  - Selectable interface voltages of 2.5 and 3.3 V
  - Parity checking on both L2 address and data
- Memory management unit
  - 128-entry, two-way set-associative instruction TLB
  - 128-entry, two-way set-associative data TLB
  - Hardware reload for TLBs
  - Hardware or optional software tablewalk support
  - Eight instruction BATs and eight data BATs
  - Eight SPRGs, for assistance with software tablewalks
  - Virtual memory support for up to 4 exabytes (2^{52}) of virtual memory
  - Real memory support for up to 4 gigabytes (2^{32}) of physical memory
- Bus interface
  - Compatible with 60x processor interface
  - 32-bit address bus
  - 64-bit data bus, 32-bit mode selectable
  - Bus-to-core frequency multipliers of 2x, 3x, 3.5x, 4x, 4.5x, 5x, 5.5x, 6x, 6.5x, 7x, 7.5x, 8x, 10x supported
  - Selectable interface voltages of 2.5 and 3.3 V
  - Parity checking on both address and data buses
- Power management
  - Low-power design with thermal requirements very similar to MPC740/MPC750
  - Three static power saving modes: doze, nap, and sleep
  - Dynamic power management
- Integrated thermal management assist unit
  - On-chip thermal sensor and control logic
  - Thermal management interrupt for software regulation of junction temperature
- Testability
  - LSSD scan design
  - IEEE 1149.1 JTAG interface

3 General Parameters

The following list provides a summary of the general parameters of the MPC755:

Technology	0.22 µm CMOS, six-layer metal
Die size	6.61 mm × 7.73 mm (51 mm^2)
Transistor count	6.75 million
Logic design	Fully-static

Table 4. Package Thermal Characteristics [6]

Characteristic	Symbol	Value			Unit	Notes
		MPC755 CBGA	MPC755 PBGA	MPC745 PBGA		
Junction-to-ambient thermal resistance, natural convection	$R_{\theta JA}$	24	31	34	°C/W	1, 2
Junction-to-ambient thermal resistance, natural convection, four-layer (2s2p) board	$R_{\theta JMA}$	17	25	26	°C/W	1, 3
Junction-to-ambient thermal resistance, 200 ft/min airflow, single-layer (1s) board	$R_{\theta JMA}$	18	25	27	°C/W	1, 3
Junction-to-ambient thermal resistance, 200 ft/min airflow, four-layer (2s2p) board	$R_{\theta JMA}$	14	21	22	°C/W	1, 3
Junction-to-board thermal resistance	$R_{\theta JB}$	8	17	17	°C/W	4
Junction-to-case thermal resistance	$R_{\theta JC}$	<0.1	<0.1	<0.1	°C/W	5

Notes:

1. Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the calculated case temperature. The actual value of $R_{\theta JC}$ for the part is less than 0.1°C/W.
6. Refer to Section 8.8, "Thermal Management Information," for more details about thermal management.

The MPC755 incorporates a thermal management assist unit (TAU) composed of a thermal sensor, digital-to-analog converter, comparator, control logic, and dedicated special-purpose registers (SPRs). See the *MPC750 RISC Microprocessor Family User's Manual* for more information on the use of this feature. Specifications for the thermal sensor portion of the TAU are found in Table 5.

Table 5. Thermal Sensor Specifications

At recommended operating conditions (see Table 3)

Characteristic	Min	Max	Unit	Notes
Temperature range	0	127	°C	1
Comparator settling time	20	—	µs	2, 3
Resolution	4	—	°C	3
Accuracy	–12	+12	°C	3

Notes:

1. The temperature is the junction temperature of the die. The thermal assist unit's raw output does not indicate an absolute temperature, but must be interpreted by software to derive the absolute junction temperature. For information about the use and calibration of the TAU, see Freescale Application Note AN1800/D, *Programming the Thermal Assist Unit in the MPC750 Microprocessor.*
2. The comparator settling time value must be converted into the number of CPU clocks that need to be written into the THRM3 SPR.
3. Guaranteed by design and characterization.

Table 6 provides the DC electrical characteristics for the MPC755.

Table 6. DC Electrical Specifications

At recommended operating conditions (see Table 3)

Characteristic	Nominal Bus Voltage [1]	Symbol	Min	Max	Unit	Notes
Input high voltage (all inputs except SYSCLK)	2.5	V_{IH}	1.6	(L2)OV_{DD} + 0.3	V	2, 3
	3.3	V_{IH}	2.0	(L2)OV_{DD} + 0.3	V	2, 3
Input low voltage (all inputs except SYSCLK)	2.5	V_{IL}	–0.3	0.6	V	2
	3.3	V_{IL}	–0.3	0.8	V	
SYSCLK input high voltage	2.5	KV_{IH}	1.8	OV_{DD} + 0.3	V	
	3.3	KV_{IH}	2.4	OV_{DD} + 0.3	V	
SYSCLK input low voltage	2.5	KV_{IL}	–0.3	0.4	V	
	3.3	KV_{IL}	–0.3	0.4	V	
Input leakage current, V_{in} = L2OV_{DD}/OV_{DD}		I_{in}	—	10	µA	2, 3
High-Z (off-state) leakage current, V_{in} = L2OV_{DD}/OV_{DD}		I_{TSI}	—	10	µA	2, 3, 5
Output high voltage, I_{OH} = –6 mA	2.5	V_{OH}	1.7	—	V	
	3.3	V_{OH}	2.4	—	V	
Output low voltage, I_{OL} = 6 mA	2.5	V_{OL}	—	0.45	V	
	3.3	V_{OL}	—	0.4	V	

4.2 AC Electrical Characteristics

This section provides the AC electrical characteristics for the MPC755. After fabrication, functional parts are sorted by maximum processor core frequency as shown in Section 4.2.1, "Clock AC Specifications," and tested for conformance to the AC specifications for that frequency. The processor core frequency is determined by the bus (SYSCLK) frequency and the settings of the PLL_CFG[0:3] signals. Parts are sold by maximum processor core frequency; see Section 10, "Ordering Information."

4.2.1 Clock AC Specifications

Table 8 provides the clock AC timing specifications as defined in Figure 3.

Table 8. Clock AC Timing Specifications

At recommended operating conditions (see Table 3)

Characteristic	Symbol	Maximum Processor Core Frequency						Unit	Notes
		300 MHz		350 MHz		400 MHz			
		Min	Max	Min	Max	Min	Max		
Processor frequency	f_{core}	200	300	200	350	200	400	MHz	1
VCO frequency	f_{VCO}	400	600	400	700	400	800	MHz	1
SYSCLK frequency	f_{SYSCLK}	25	100	25	100	25	100	MHz	1
SYSCLK cycle time	t_{SYSCLK}	10	40	10	40	10	40	ns	
SYSCLK rise and fall time	t_{KR}, t_{KF}	—	2.0	—	2.0	—	2.0	ns	2
	t_{KR}, t_{KF}	—	1.4	—	1.4	—	1.4	ns	2
SYSCLK duty cycle measured at $OV_{DD}/2$	t_{KHKL}/t_{SYSCLK}	40	60	40	60	40	60	%	3
SYSCLK jitter		—	±150	—	±150	—	±150	ps	3, 4
Internal PLL relock time		—	100	—	100	—	100	μs	3, 5

Notes:

1. **Caution:** The SYSCLK frequency and PLL_CFG[0:3] settings must be chosen such that the resulting SYSCLK (bus) frequency, CPU (core) frequency, and PLL (VCO) frequency do not exceed their respective maximum or minimum operating frequencies. Refer to the PLL_CFG[0:3] signal description in Section 8.1, "PLL Configuration," for valid PLL_CFG[0:3] settings.
2. Rise and fall times measurements are now specified in terms of slew rates, rather than time to account for selectable I/O bus interface levels. The minimum slew rate of 1 V/ns is equivalent to a 2 ns maximum rise/fall time measured at 0.4 and 2.4 V (OV_{DD} = 3.3 V) or a rise/fall time of 1 ns measured at 0.4 and 1.8 V (OV_{DD} = 2.5 V).
3. Timing is guaranteed by design and characterization.
4. This represents total input jitter—short term and long term combined—and is guaranteed by design.
5. Relock timing is guaranteed by design and characterization. PLL-relock time is the maximum amount of time required for PLL lock after a stable V_{DD} and SYSCLK are reached during the power-on reset sequence. This specification also applies when the PLL has been disabled and subsequently re-enabled during sleep mode. Also note that $\overline{\text{HRESET}}$ must be held asserted for a minimum of 255 bus clocks after the PLL-relock time during the power-on reset sequence.

Figure 3 provides the SYSCLK input timing diagram.

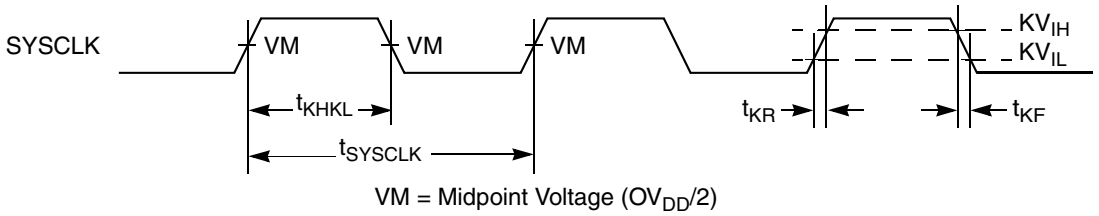


Figure 3. SYSCLK Input Timing Diagram

4.2.2 Processor Bus AC Specifications

Table 9 provides the processor bus AC timing specifications for the MPC755 as defined in Figure 4 and Figure 6. Timing specifications for the L2 bus are provided in Section 4.2.3, "L2 Clock AC Specifications."

Table 9. Processor Bus Mode Selection AC Timing Specifications [1]

At recommended operating conditions (see Table 3)

Parameter	Symbol [2]	All Speed Grades		Unit	Notes
		Min	Max		
Mode select input setup to $\overline{\text{HRESET}}$	t_{MVRH}	8	—	t_{sysclk}	3, 4, 5, 6, 7
$\overline{\text{HRESET}}$ to mode select input hold	t_{MXRH}	0	—	ns	3, 4, 6, 7, 8

Notes:

1. All input specifications are measured from the midpoint of the signal in question to the midpoint of the rising edge of the input SYSCLK. All output specifications are measured from the midpoint of the rising edge of SYSCLK to the midpoint of the signal in question. All output timings assume a purely resistive 50-Ω load (see Figure 5). Input and output timings are measured at the pin; time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbology used for timing specifications herein follows the pattern of $t_{\text{(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(reference)(state)(signal)(state)}}$ for outputs. For example, t_{IVKH} symbolizes the time input signals (I) reach the valid state (V) relative to the SYSCLK reference (K) going to the high (H) state or input setup time. And t_{KHOV} symbolizes the time from SYSCLK (K) going high (H) until outputs (O) are valid (V) or output valid time. Input hold time can be read as the time that the input signal (I) went invalid (X) with respect to the rising clock edge (KH)—note the position of the reference and its state for inputs—and output hold time can be read as the time from the rising edge (KH) until the output went invalid (OX).
3. The setup and hold time is with respect to the rising edge of $\overline{\text{HRESET}}$ (see Figure 4).
4. This specification is for configuration mode select only. Also note that the $\overline{\text{HRESET}}$ must be held asserted for a minimum of 255 bus clocks after the PLL-relock time during the power-on reset sequence.
5. t_{sysclk} is the period of the external clock (SYSCLK) in ns. The numbers given in the table must be multiplied by the period of SYSCLK to compute the actual time duration (in ns) of the parameter in question.
6. Mode select signals are BVSEL, L2VSEL, PLL_CFG[0:3], and $\overline{\text{TLBISYNC}}$.
7. Guaranteed by design and characterization.
8. Bus mode select pins must remain stable during operation. Changing the logic states of BVSEL or L2VSEL during operation will cause the bus mode voltage selection to change. Changing the logic states of the PLL_CFG pins during operation will cause the PLL division ratio selection to change. Both of these conditions are considered outside the specification and are not supported. Once $\overline{\text{HRESET}}$ is negated the states of the bus mode selection pins must remain stable.

Table 11. L2CLK Output AC Timing Specification

At recommended operating conditions (see Table 3)

Parameter	Symbol	All Speed Grades		Unit	Notes
		Min	Max		
L2CLK frequency	f_{L2CLK}	80	450	MHz	1, 4
L2CLK cycle time	t_{L2CLK}	2.5	12.5	ns	
L2CLK duty cycle	t_{CHCL}/t_{L2CLK}	45	55	%	2, 7
Internal DLL-relock time		640	—	L2CLK	3, 7
DLL capture window		0	10	ns	5, 7
L2CLK_OUT output-to-output skew	t_{L2CSKW}	—	50	ps	6, 7
L2CLK_OUT output jitter		—	±150	ps	6, 7

Notes:

1. L2CLK outputs are L2CLK_OUTA, L2CLK_OUTB, L2CLK_OUT, and L2SYNC_OUT pins. The L2CLK frequency-to-core frequency settings must be chosen such that the resulting L2CLK frequency and core frequency do not exceed their respective maximum or minimum operating frequencies. The maximum L2LCK frequency will be system dependent. L2CLK_OUTA and L2CLK_OUTB must have equal loading.
2. The nominal duty cycle of the L2CLK is 50% measured at midpoint voltage.
3. The DLL-relock time is specified in terms of L2CLK periods. The number in the table must be multiplied by the period of L2CLK to compute the actual time duration in ns. Relock timing is guaranteed by design and characterization.
4. The L2CR[L2SL] bit should be set for L2CLK frequencies less than 110 MHz. This adds more delay to each tap of the DLL.
5. Allowable skew between L2SYNC_OUT and L2SYNC_IN.
6. This output jitter number represents the maximum delay of one tap forward or one tap back from the current DLL tap as the phase comparator seeks to minimize the phase difference between L2SYNC_IN and the internal L2CLK. This number must be comprehended in the L2 timing analysis. The input jitter on SYSCLK affects L2CLK_OUT and the L2 address/data/control signals equally and, therefore, is already comprehended in the AC timing and does not have to be considered in the L2 timing analysis.
7. Guaranteed by design.

The L2CLK_OUT timing diagram is shown in Figure 7.

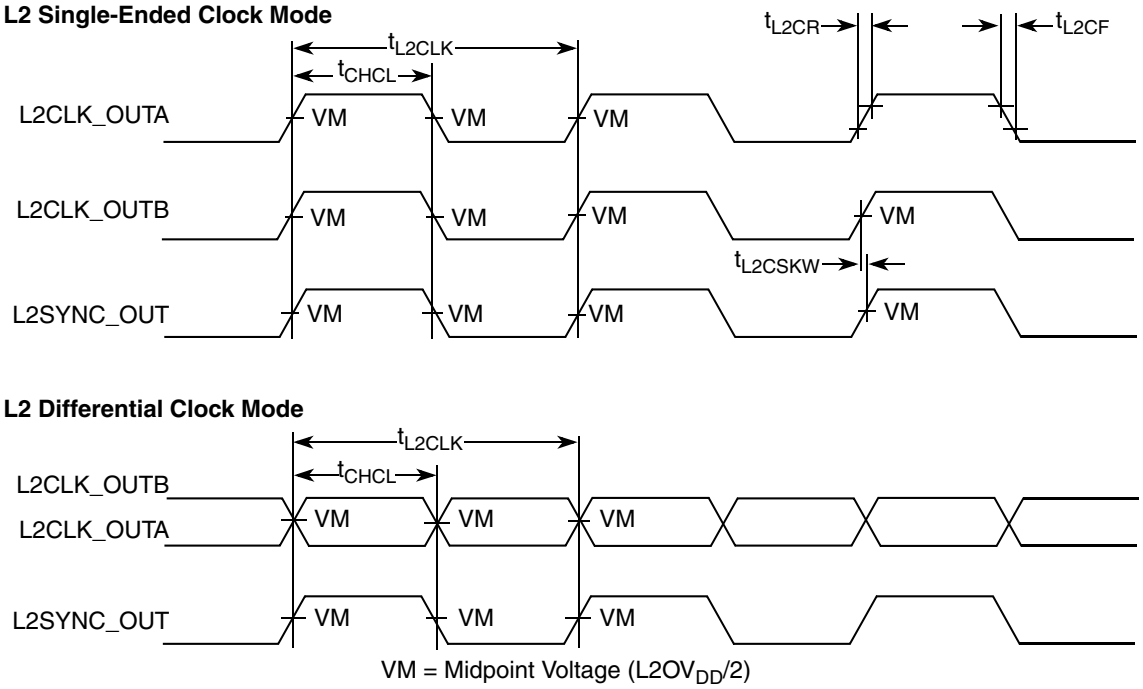


Figure 7. L2CLK_OUT Output Timing Diagram

4.2.4 L2 Bus AC Specifications

Table 12 provides the L2 bus interface AC timing specifications for the MPC755 as defined in Figure 8 and Figure 9 for the loading conditions described in Figure 10.

Table 12. L2 Bus Interface AC Timing Specifications

At recommended operating conditions (see Table 3)

Parameter	Symbol	All Speed Grades		Unit	Notes
		Min	Max		
L2SYNC_IN rise and fall time	t_{L2CR}, t_{L2CF}	—	1.0	ns	1
Setup times: Data and parity	t_{DVL2CH}	1.2	—	ns	2
Input hold times: Data and parity	t_{DXL2CH}	0	—	ns	2
Valid times: All outputs when L2CR[14–15] = 00 All outputs when L2CR[14–15] = 01 All outputs when L2CR[14–15] = 10 All outputs when L2CR[14–15] = 11	t_{L2CHOV}	 — — — —	 3.1 3.2 3.3 3.7	ns	3, 4
Output hold times: All outputs when L2CR[14–15] = 00 All outputs when L2CR[14–15] = 01 All outputs when L2CR[14–15] = 10 All outputs when L2CR[14–15] = 11	t_{L2CHOX}	 0.5 0.7 0.9 1.1	 — — — —	ns	3

4.2.5 IEEE 1149.1 AC Timing Specifications

Table 13 provides the IEEE 1149.1 (JTAG) AC timing specifications as defined in Figure 12 through Figure 15.

Table 13. JTAG AC Timing Specifications (Independent of SYSCLK) [1]

At recommended operating conditions (see Table 3)

Parameter		Symbol	Min	Max	Unit	Notes
TCK frequency of operation		f_{TCLK}	0	16	MHz	
TCK cycle time		t_{TCLK}	62.5	—	ns	
TCK clock pulse width measured at 1.4 V		t_{JHJL}	31	—	ns	
TCK rise and fall times		t_{JR}, t_{JF}	0	2	ns	
$\overline{\text{TRST}}$ assert time		t_{TRST}	25	—	ns	2
Input setup times:	Boundary-scan data TMS, TDI	t_{DVJH} t_{IVJH}	4 0	— —	ns	3
Input hold times:	Boundary-scan data TMS, TDI	t_{DXJH} t_{IXJH}	15 12	— —	ns	3
Valid times:	Boundary-scan data TDO	t_{JLDV} t_{JLOV}	— —	4 4	ns	4
Output hold times:	Boundary-scan data TDO	t_{JLDH} t_{JLOH}	25 12	— —	ns	4
TCK to output high impedance:	Boundary-scan data TDO	t_{JLDZ} t_{JLOZ}	3 3	19 9	ns	4, 5

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of TCLK to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 11). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal which must be asserted for this minimum time to be recognized.
3. Non-JTAG signal input timing with respect to TCK.
4. Non-JTAG signal output timing with respect to TCK.
5. Guaranteed by design and characterization.

Figure 11 provides the AC test load for TDO and the boundary-scan outputs of the MPC755.

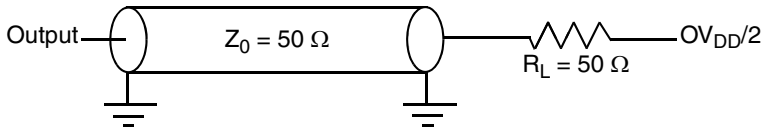


Figure 11. AC Test Load for the JTAG Interface

Table 14. Pinout Listing for the MPC745, 255 PBGA Package (continued)

Signal Name	Pin Number	Active	I/O	I/F Voltage [1]	Notes
$\overline{\text{INT}}$	B15	Low	Input	OV_{DD}	
L1_TSTCLK	D11	High	Input	—	2
L2_TSTCLK	D12	High	Input	—	2
$\overline{\text{LSSD\_MODE}}$	B10	Low	Input	—	2
$\overline{\text{MCP}}$	C13	Low	Input	OV_{DD}	
NC (No Connect)	B7, B8, C3, C6, C8, D5, D6, H4, J16, A4, A5, A2, A3, B5	—	—	—	
OV_{DD}	C7, E5, E7, E10, E12, G3, G5, G12, G14, K3, K5, K12, K14, M5, M7, M10, M12, P7, P10	—	—	2.5 V/3.3 V	
PLL_CFG[0:3]	A8, B9, A9, D9	High	Input	OV_{DD}	
$\overline{\text{QACK}}$	D3	Low	Input	OV_{DD}	
$\overline{\text{QREQ}}$	J3	Low	Output	OV_{DD}	
$\overline{\text{RSRV}}$	D1	Low	Output	OV_{DD}	
$\overline{\text{SMI}}$	A16	Low	Input	OV_{DD}	
$\overline{\text{SRESET}}$	B14	Low	Input	OV_{DD}	
SYSCLK	C9	—	Input	OV_{DD}	
$\overline{\text{TA}}$	H14	Low	Input	OV_{DD}	
TBEN	C2	High	Input	OV_{DD}	
$\overline{\text{TBST}}$	A14	Low	I/O	OV_{DD}	
TCK	C11	High	Input	OV_{DD}	
TDI	A11	High	Input	OV_{DD}	5
TDO	A12	High	Output	OV_{DD}	
$\overline{\text{TEA}}$	H13	Low	Input	OV_{DD}	
$\overline{\text{TLBISYNC}}$	C4	Low	Input	OV_{DD}	
TMS	B11	High	Input	OV_{DD}	5
$\overline{\text{TRST}}$	C10	Low	Input	OV_{DD}	5
$\overline{\text{TS}}$	J13	Low	I/O	OV_{DD}	
TSIZ[0:2]	A13, D10, B12	High	Output	OV_{DD}	
TT[0:4]	B13, A15, B16, C14, C15	High	I/O	OV_{DD}	
$\overline{\text{WT}}$	D2	Low	Output	OV_{DD}	
V_{DD}	F6, F8, F9, F11, G7, G10, H6, H8, H9, H11, J6, J8, J9, J11, K7, K10, L6, L8, L9, L11	—	—	2.0 V	

Table 15. Pinout Listing for the MPC755, 360 BGA Package (continued)

Signal Name	Pin Number	Active	I/O	I/F Voltage [1]	Notes
DH[0:31]	W12, W11, V11, T9, W10, U9, U10, M11, M9, P8, W7, P9, W9, R10, W6, V7, V6, U8, V9, T7, U7, R7, U6, W5, U5, W4, P7, V5, V4, W3, U4, R5	High	I/O	OV_{DD}	
DL[0:31]	M6, P3, N4, N5, R3, M7, T2, N6, U2, N7, P11, V13, U12, P12, T13, W13, U13, V10, W8, T11, U11, V12, V8, T1, P1, V1, U1, N1, R2, V3, U3, W2	High	I/O	OV_{DD}	
DP[0:7]	L1, P2, M2, V2, M1, N2, T3, R1	High	I/O	OV_{DD}	
$\overline{\text{DRTRY}}$	H6	Low	Input	OV_{DD}	
$\overline{\text{GBL}}$	B1	Low	I/O	OV_{DD}	
GND	D10, D14, D16, D4, D6, E12, E8, F4, F6, F10, F14, F16, G9, G11, H5, H8, H10, H12, H15, J9, J11, K4, K6, K8, K10, K12, K14, K16, L9, L11, M5, M8, M10, M12, M15, N9, N11, P4, P6, P10, P14, P16, R8, R12, T4, T6, T10, T14, T16	—	—	GND	
$\overline{\text{HRESET}}$	B6	Low	Input	OV_{DD}	
$\overline{\text{INT}}$	C11	Low	Input	OV_{DD}	
L1_TSTCLK	F8	High	Input	—	2
L2ADDR[16:0]	G18, H19, J13, J14, H17, H18, J16, J17, J18, J19, K15, K17, K18, M19, L19, L18, L17	High	Output	$L2OV_{DD}$	
$L2AV_{DD}$	L13	—	—	2.0 V	
$\overline{\text{L2CE}}$	P17	Low	Output	$L2OV_{DD}$	
L2CLK_OUTA	N15	—	Output	$L2OV_{DD}$	
L2CLK_OUTB	L16	—	Output	$L2OV_{DD}$	
L2DATA[0:63]	U14, R13, W14, W15, V15, U15, W16, V16, W17, V17, U17, W18, V18, U18, V19, U19, T18, T17, R19, R18, R17, R15, P19, P18, P13, N14, N13, N19, N17, M17, M13, M18, H13, G19, G16, G15, G14, G13, F19, F18, F13, E19, E18, E17, E15, D19, D18, D17, C18, C17, B19, B18, B17, A18, A17, A16, B16, C16, A14, A15, C15, B14, C14, E13	High	I/O	$L2OV_{DD}$	
L2DP[0:7]	V14, U16, T19, N18, H14, F17, C19, B15	High	I/O	$L2OV_{DD}$	
$L2OV_{DD}$	D15, E14, E16, H16, J15, L15, M16, P15, R14, R16, T15, F15	—	—	$L2OV_{DD}$	
L2SYNC_IN	L14	—	Input	$L2OV_{DD}$	
L2SYNC_OUT	M14	—	Output	$L2OV_{DD}$	
L2_TSTCLK	F7	High	Input	—	2
L2VSEL	A19	High	Input	$L2OV_{DD}$	1, 5, 6, 7
$\overline{\text{L2WE}}$	N16	Low	Output	$L2OV_{DD}$	

Table 15. Pinout Listing for the MPC755, 360 BGA Package (continued)

Signal Name	Pin Number	Active	I/O	I/F Voltage [1]	Notes
L2ZZ	G17	High	Output	$L2OV_{DD}$	
$\overline{\text{LSSD\_MODE}}$	F9	Low	Input	—	2
$\overline{\text{MCP}}$	B11	Low	Input	OV_{DD}	
NC (No Connect)	B3, B4, B5, W19, K9, K11 [4], K19 [4]	—	—	—	
OV_{DD}	D5, D8, D12, E4, E6, E9, E11, F5, H4, J5, L5, M4, P5, R4, R6, R9, R11, T5, T8, T12	—	—	OV_{DD}	
PLL_CFG[0:3]	A4, A5, A6, A7	High	Input	OV_{DD}	
$\overline{\text{QACK}}$	B2	Low	Input	OV_{DD}	
$\overline{\text{QREQ}}$	J3	Low	Output	OV_{DD}	
$\overline{\text{RSRV}}$	D3	Low	Output	OV_{DD}	
$\overline{\text{SMI}}$	A12	Low	Input	OV_{DD}	
$\overline{\text{SRESET}}$	E10	Low	Input	OV_{DD}	
SYSCLK	H9	—	Input	OV_{DD}	
$\overline{\text{TA}}$	F1	Low	Input	OV_{DD}	
TBEN	A2	High	Input	OV_{DD}	
$\overline{\text{TBST}}$	A11	Low	I/O	OV_{DD}	
TCK	B10	High	Input	OV_{DD}	
TDI	B7	High	Input	OV_{DD}	6
TDO	D9	High	Output	OV_{DD}	
$\overline{\text{TEA}}$	J1	Low	Input	OV_{DD}	
$\overline{\text{TLBISYNC}}$	A3	Low	Input	OV_{DD}	
TMS	C8	High	Input	OV_{DD}	6
$\overline{\text{TRST}}$	A10	Low	Input	OV_{DD}	6
$\overline{\text{TS}}$	K7	Low	I/O	OV_{DD}	
TSIZ[0:2]	A9, B9, C9	High	Output	OV_{DD}	
TT[0:4]	C10, D11, B12, C12, F11	High	I/O	OV_{DD}	
$\overline{\text{WT}}$	C3	Low	Output	OV_{DD}	
V_{DD}	G8, G10, G12, J8, J10, J12, L8, L10, L12, N8, N10, N12	—	—	2.0 V	

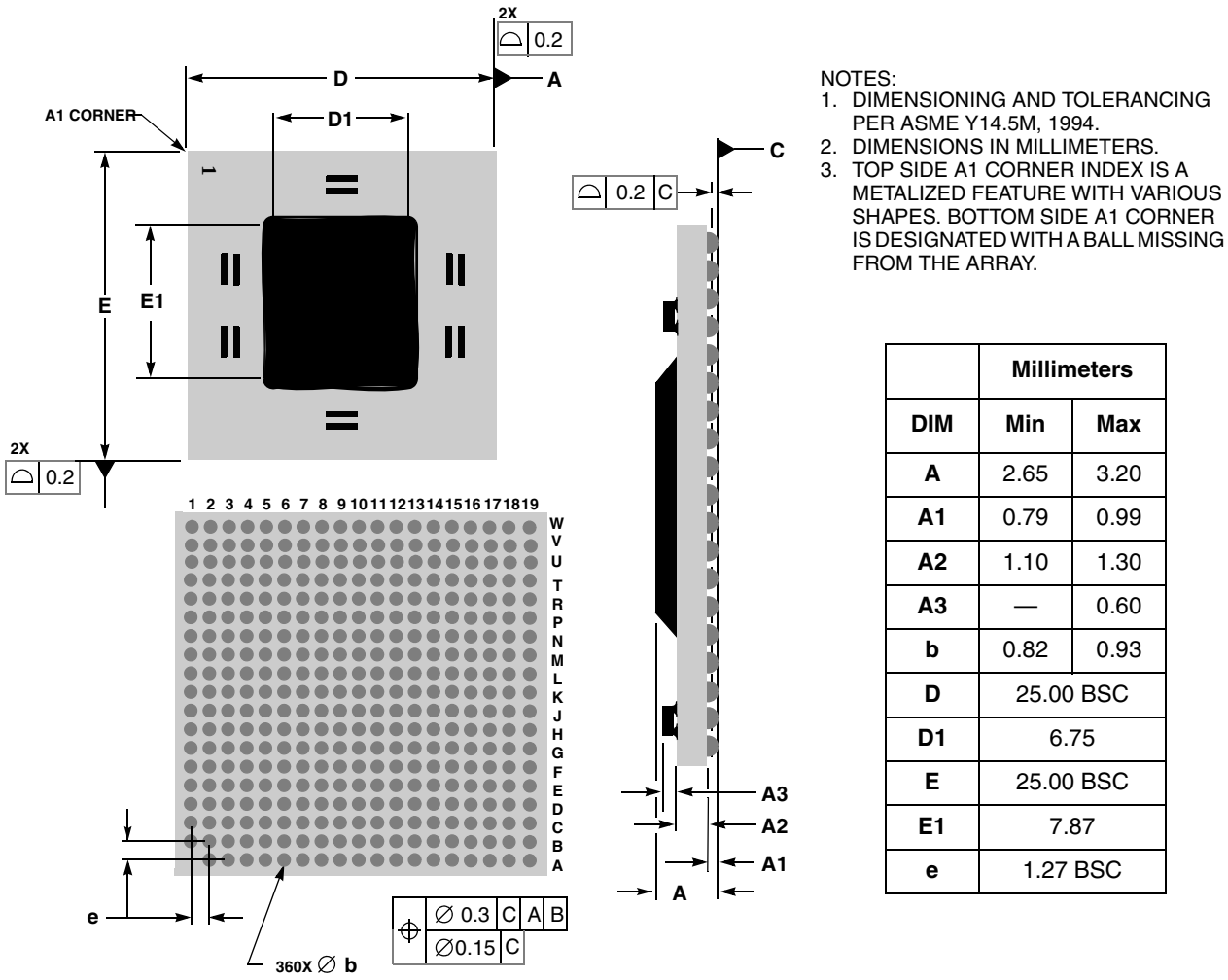
7.3 Package Parameters for the MPC755 CBGA

The package parameters are as provided in the following list. The package type is 25 × 25 mm, 360-lead ceramic ball grid array (CBGA).

Package outline	25 × 25 mm
Interconnects	360 (19 × 19 ball array – 1)
Pitch	1.27 mm (50 mil)
Minimum module height	2.65 mm
Maximum module height	3.20 mm
Ball diameter	0.89 mm (35 mil)

7.4 Mechanical Dimensions for the MPC755 CBGA

Figure 19 provides the mechanical dimensions and bottom surface nomenclature for the MPC755, 360 CBGA package.



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. DIMENSIONS IN MILLIMETERS.
3. TOP SIDE A1 CORNER INDEX IS A METALIZED FEATURE WITH VARIOUS SHAPES. BOTTOM SIDE A1 CORNER IS DESIGNATED WITH A BALL MISSING FROM THE ARRAY.

	Millimeters	
DIM	Min	Max
A	2.65	3.20
A1	0.79	0.99
A2	1.10	1.30
A3	—	0.60
b	0.82	0.93
D	25.00 BSC	
D1	6.75	
E	25.00 BSC	
E1	7.87	
e	1.27 BSC	

Figure 19. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC755, 360 CBGA Package

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0508 or 0603 orientations where connections are made along the length of the part.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, $L2OV_{DD}$, and OV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors:100–330 µF (AVX TPS tantalum or Sanyo OSCON).

8.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level through a resistor. Unused active low inputs should be tied to OV_{DD}. Unused active high inputs should be connected to GND. All NC (no connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD}, OV_{DD}, $L2OV_{DD}$, and GND pins of the MPC755. Note that power must be supplied to $L2OV_{DD}$ even if the L2 interface of the MPC755 will not be used; it is recommended to connect $L2OV_{DD}$ to OV_{DD} and L2VSEL to BVSEL if the L2 interface is unused. (This requirement does not apply to the MPC745 since it has neither an L2 interface nor $L2OV_{DD}$ pins.)

8.5 Output Buffer DC Impedance

The MPC755 60x and L2 I/O drivers are characterized over process, voltage, and temperature. To measure Z_0, an external resistor is connected from the chip pad to $(L2)OV_{DD}$ or GND. Then, the value of each resistor is varied until the pad voltage is $(L2)OV_{DD}/2$ (see Figure 22).

The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held low, SW2 is closed (SW1 is open), and R_N is trimmed until the voltage at the pad equals $(L2)OV_{DD}/2$. R_N then becomes the resistance of the pull-down devices. When data is held high, SW1 is closed (SW2 is open), and R_P is trimmed until the voltage at the pad equals $(L2)OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices.

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Thermagon Inc. 888-246-9050
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Cleveland, OH 44102
Internet: www.thermagon.com

8.8.3 Heat Sink Selection Example

This section provides a heat sink selection example using one of the commercially-available heat sinks. For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

$$T_j = T_a + T_r + (\theta_{jc} + \theta_{int} + \theta_{sa}) \times P_d$$

where:

T_j is the die-junction temperature
T_a is the inlet cabinet ambient temperature
T_r is the air temperature rise within the computer cabinet
θ_{jc} is the junction-to-case thermal resistance
θ_{int} is the adhesive or interface material thermal resistance
θ_{sa} is the heat sink base-to-ambient thermal resistance
P_d is the power dissipated by the device

During operation the die-junction temperatures (T_j) should be maintained less than the value specified in Table 3. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_a) may range from 30° to 40°C. The air temperature rise within a cabinet (T_r) may be in the range of 5° to 10°C. The thermal resistance of the thermal interface material (θ_{int}) is typically about 1°C/W. Assuming a T_a of 30°C, a T_r of 5°C, a CBGA package $R_{\theta jc} < 0.1$, and a power consumption (P_d) of 5.0 W, the following expression for T_j is obtained:

Die-junction temperature: $T_j = 30°C + 5°C + (0.1°C/W + 1.0°C/W + \theta_{sa}) \times 5.0\ W$

For a Thermalloy heat sink #2328B, the heat sink-to-ambient thermal resistance (θ_{sa}) versus airflow velocity is shown in Figure 28.

Assuming an air velocity of 0.5 m/s, we have an effective R_{sa} of 7°C/W, thus

$$T_j = 30°C + 5°C + (0.1°C/W + 1.0°C/W + 7°C/W) \times 5.0\ W,$$

resulting in a die-junction temperature of approximately 76°C which is well within the maximum operating temperature of the component.

Other heat sinks offered by Aavid Thermalloy, Alpha Novatech, The Bergquist Company, IERC, Chip Coolers, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, and may or may not need airflow.

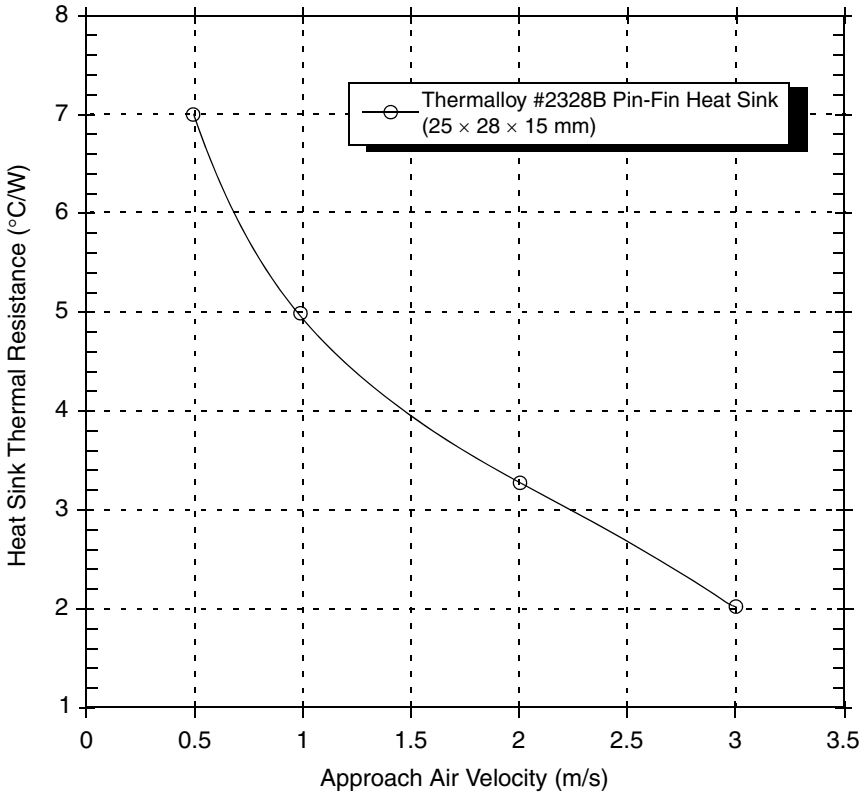

Figure 28. Thermalloy #2328B Heat Sink-to-Ambient Thermal Resistance Versus Airflow Velocity

Though the die junction-to-ambient and the heat sink-to-ambient thermal resistances are a common figure-of-merit used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature, is not only a function of the component-level thermal resistance, but the system-level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature—airflow, board population (local heat flux of adjacent components), heat sink efficiency, heat sink attach, heat sink placement, next-level interconnect technology, system air temperature rise, altitude, etc.

Due to the complexity and the many variations of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation, convection, and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the board, as well as, system-level designs.

10 Ordering Information

Ordering information for the devices fully covered by this specification document is provided in Section 10.1, “Part Numbers Fully Addressed by This Document.” Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also includes an application modifier which may specify special application conditions. Each part number also contains a revision code which refers to the die mask revision number. Section 10.2, “Part Numbers Not Fully Addressed by This Document,” lists the part numbers which do not fully conform to the specifications of this document. These special part numbers require an additional document called a hardware specifications addendum.

10.1 Part Numbers Fully Addressed by This Document

Table 20 provides the Freescale part numbering nomenclature for the MPC755 and MPC745 devices fully addressed by this document.

Table 20. Part Numbering Nomenclature

MPC	*xxx*	*x*	*xx*	*nnn*	*x*	*x*
Product Code	**Part Identifier**	**Process Descriptor**	**Package [1]**	**Processor Frequency**	**Application Modifier**	**Revision Level**
XPC[2]	755 745	B = HiP4DP	PX = PBGA RX = CBGA	300 350	L: 2.0 V ± 100 mV 0° to 105°C	E: 2.8; PVR = 0008 3203
	755	C = HiP4DP		400		
MPC	755	B = HiP4DP		300 350		
		C = HiP4DP		350 400		
	745	B = HiP4DP	PX = PBGA	300 350		
	745	C = HiP4DP	PX = PBGA VT = PBGAPb-free BGA	350		
	755 745	B = HiP4DP	VT = PBGAPb-free BGA	300 350		
	755	C = HiP4DP		350 400		

Notes:

1. See Section 7, “Package Description,” for more information on available package types.
2. The X prefix in a Freescale part number designates a “Pilot Production Prototype” as defined by Freescale SOP 3-13. These are from a limited production volume of prototypes manufactured, tested, and Q.A. inspected on a qualified technology to simulate normal production. These parts have only preliminary reliability and characterization data. Before pilot production prototypes may be shipped, written authorization from the customer must be on file in the applicable sales office acknowledging the qualification status and the fact that product changes may still occur while shipping pilot production prototypes

10.2 Part Numbers Not Fully Addressed by This Document

Devices not fully addressed in this document are described in separate hardware specification addendums which supplement and supersede this document, as described in the following tables.

Table 21. Part Numbers Addressed by XPC755B*xxnnn*T*x* Series Part Numbers (Document No. MPC755ECSO1AD)

XPC	755	B	*xx*	*nnn*	T	*x*

Product Code	Part Identifier	Process Descriptor	Package	Processor Frequency	Application Modifier	Revision Level
XPC	755	B = HiP4DP	RX = CBGA	350 400	T: 2.0 V ± 100 mV –40° to 105°C	D: 2.7; PVR = 0008 3203 E: 2.8; PVR = 0008 3203
MPC	755	C=HiP4DP	RX = CBGA	350	T: 2.0 V ± 100 mV –40° to 105°C	E: 2.8; PVR = 0008 3203

Table 22. Part Numbers Addressed by XPC755B*xxnnn*LD Series Part Numbers (Document No. MPC755ECSO2AD)

XPC	*xxx*	B	*xx*	*nnn*	L	D

Product Code	Part Identifier	Process Descriptor	Package	Processor Frequency	Application Modifier	Revision Level
XPC	755 745	B = HiP4DP	PX = PBGA RX = CBGA	300 350 400	L: 2.0 V ± 100 mV 0° to 105°C	D: 2.7; PVR = 0008 3203

Table 23. Part Numbers Addressed by XPC755*xxxnnn*LE Series Part Numbers (Document No. MPC755ECSO3AD)

XPC	755	*x*	*xx*	*nnn*	L	E

Product Code	Part Identifier	Process Descriptor	Package	Processor Frequency	Application Modifier	Revision Level
XPC	755	B = HiP4DP	RX = CBGA	400	L: 2.0 V ± 100 mV 0° to 105°C	E: 2.8; PVR = 0008 3203
			PX = PBGA			
		C = HiP4DP	RX = CBGA	450		

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Document Number: MPC755EC
Rev. 8
02/2006

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